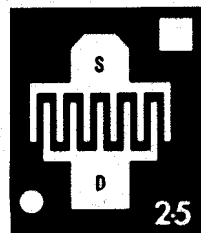


CHIP NUMBER

FN2.5



↑
.013"
(0.737mm)
↓

← .012"
(0.305mm) →

Die Size: 12 x 13 (mils)
0.305 x .0330(mm)
3 x 3 (mils)
Pad Size: 0.076 x 0.076(mm)

GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

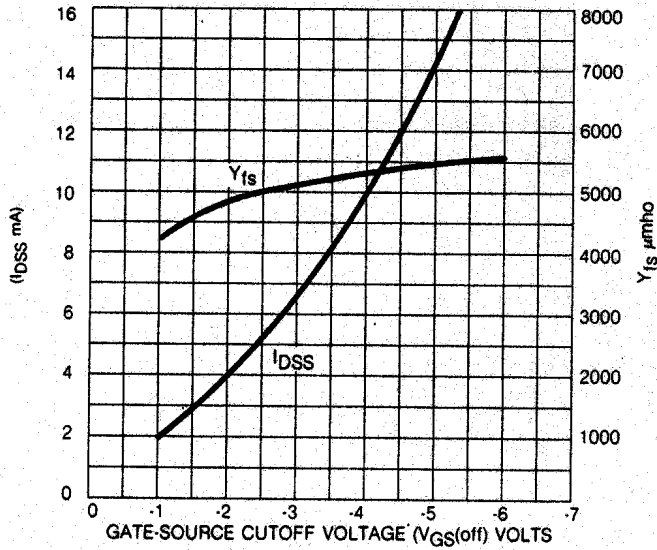
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-25	-35	-50	V	V _{DS} = 0V, I _G = 1μA
I _{DSS}	1.0	10	30	mA	V _{DS} = 15V, V _{GS} = 0
g _{fs}	3.0	5.5	7.5	mmho	V _{DS} = 15V, V _{GS} = 0
I _{GSS}		-5.0	-100	pA	V _{GS} = -20V, V _{DS} = 0
r _{DS}	100	170	500	Ω	V _{DS} = 100mV, V _{GS} = 0
V _{GS(off)}	-0.8	-3.0	8.0	V	V _{DS} = 15V, I _D = 1nA
C _{rss}	0.6	0.7	0.9	pF	V _{DS} = 15V, V _{GS} = 0, f = 1MHz
C _{iss}	3.0	3.5	4.0	pF	V _{DS} = 15V, V _{GS} = 0, f = 1MHz
ē _n		15		nV/√Hz	V _{DG} = 15V, I _D = 5.0A, f = 100Hz

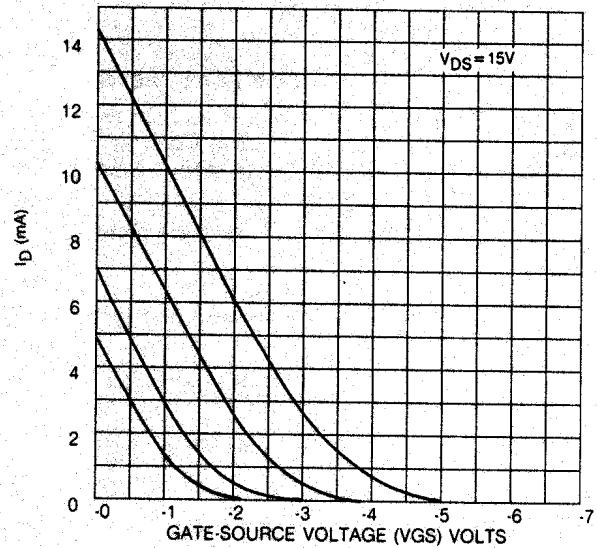
TYPICAL DEVICE TYPES: 2N4116, 2N3823, 2N3452, 2N5104, 2N5105, UC734, 2N5485

CHIP TYPE FN2.5

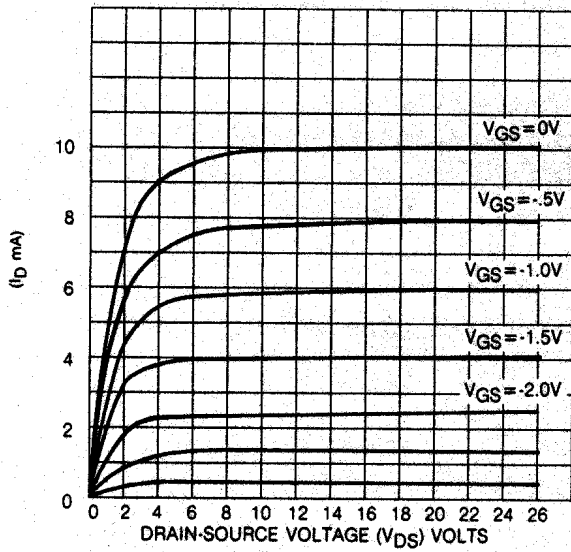
TRANSFER ADMITTANCE VS
GATE-SOURCE CUTOFF VOLTAGE



TRANSFER CHARACTERISTICS



OUTPUT CHARACTERISTICS



NORMALIZED FORWARD TRANSFER ADMITTANCE
VS TEMPERATURE

